

NCE N-Channel Enhancement Mode Power MOSFET

Description

The NCE0140KA uses advanced trench technology and design to provide excellent R_{DS(ON)} with low gate charge. It can be used in a wide variety of applications.

General Features

V_{DS} = 100V,I_D =40A

 $R_{DS(ON)} < 17m\Omega @ V_{GS}=10V (Typ:12m\Omega)$

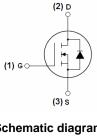
 $R_{DS(ON)} < 18m\Omega @ V_{GS}=4.5V$ (Typ:13m Ω)

- Special process technology for high ESD capability
- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation

Application

- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible power supply

100% UIS TESTED! 100% AVds TESTED!



Schematic diagram



Marking and pin assignment



TO-252-2L top view

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCE0140KA	NCE0140KA	TO-252-2L	-	-	-

Absolute Maximum Ratings (T_C=25 ℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	100	V
Gate-Source Voltage	V _{GS}	±20	V
Drain Current-Continuous	I _D	40	Α
Drain Current-Continuous(T _C =100 °C)	I _D (100℃)	28	Α
Pulsed Drain Current	I _{DM}	160	Α
Maximum Power Dissipation	P _D	140	W
Derating factor	-	0.93	W/°C
Single pulse avalanche energy (Note 5)	E _{AS}	400	mJ
Operating Junction and Storage Temperature Range	T_{J}, T_{STG}	-55 To 175	$^{\circ}$ C

Thermal Characteristic

Thermal Resistance, Junction-to-Case ^(Note 2)	R _{eJC}	1.07	°C/W

Electrical Characteristics (T_C=25 [°]C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit	
Off Characteristics	1		•				
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	100	110	-	V	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =100V,V _{GS} =0V -		-	1	μA	
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V	-	-	±100	nA	
On Characteristics (Note 3)							
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} ,I _D =250μA	0.9	1.1	1.5	V	
Drain-Source On-State Resistance	О	V _{GS} =10V, I _D =20A	-	12	17	mΩ	
Diam-Source On-State Resistance	R _{DS(ON)}	V _{GS} =4.5V, I _D =20A	-	13	18	11152	
Forward Transconductance	g FS	V_{DS} =5 V , I_{D} =20 A	32	-	ı	S	
Dynamic Characteristics (Note4)							
Input Capacitance	C _{lss}	V _{DS} =50V,V _{GS} =0V,	-	3762	ı	PF	
Output Capacitance	Coss	F=1.0MHz	-	295	ı	PF	
Reverse Transfer Capacitance	C _{rss}	1 - 1.0IVII 12	=	218	ı	PF	
Switching Characteristics (Note 4)							
Turn-on Delay Time	t _{d(on)}		-	15	ı	nS	
Turn-on Rise Time	t _r	V_{DD} =30V, R_L =1.5 Ω ,	-	11	-	nS	
Turn-Off Delay Time	$t_{d(off)}$	R_G =2.5 Ω , V_{GS} =10 V	-	52	-	nS	
Turn-Off Fall Time	t _f		-	13	-	nS	
Total Gate Charge	Qg		-	96.7	-	nC	
Gate-Source Charge	Q_{gs}	I _D =20A,V _{DD} =50V,V _{GS} =10V	-	15.3	-	nC	
Gate-Drain Charge	Q_{gd}		-	25.4	-	nC	
Drain-Source Diode Characteristics							
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =20A	-	0.85	1.2	V	
Diode Forward Current (Note 2)	Is		-	-	40	Α	
Reverse Recovery Time	t _{rr}	T _J = 25°C, I _F = 20A	-	33		nS	
Reverse Recovery Charge	Qrr	di/dt = 100A/µs ^(Note3)	-	54		nC	
Forward Turn-On Time	t _{on}	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)					

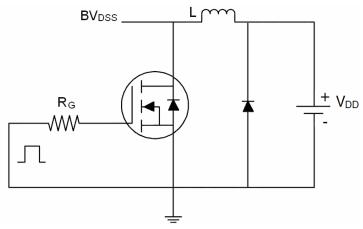
Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- **2.** Surface Mounted on FR4 Board, $t \le 10$ sec.
- 3. Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2%.
- 4. Guaranteed by design, not subject to production
- **5.** EAS condition: Tj=25 $^{\circ}$ C,V_{DD}=50V,V_G=10V,L=0.5mH,Rg=25 Ω

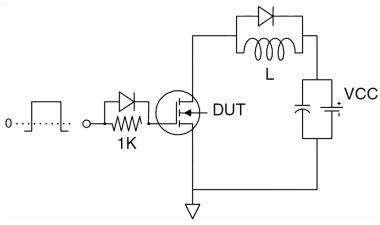


Test Circuit

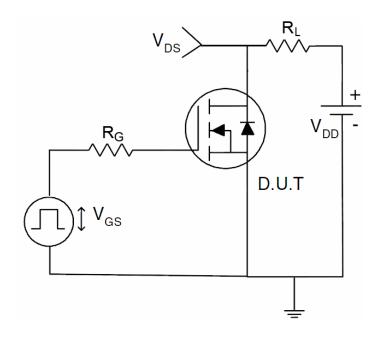
1) E_{AS} test Circuit



2) Gate charge test Circuit



3) Switch Time Test Circuit





Typical Electrical and Thermal Characteristics (Curves)

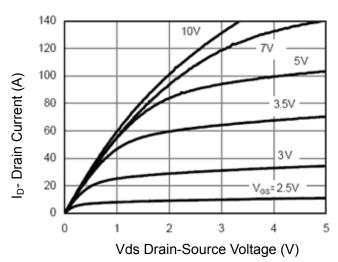


Figure 1 Output Characteristics

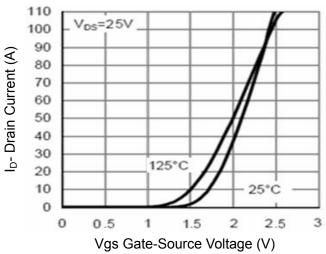


Figure 2 Transfer Characteristics

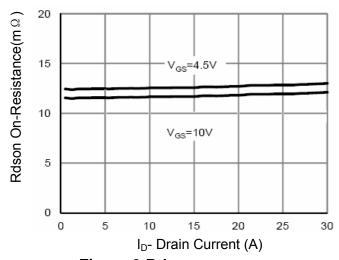


Figure 3 Rdson- Drain Current

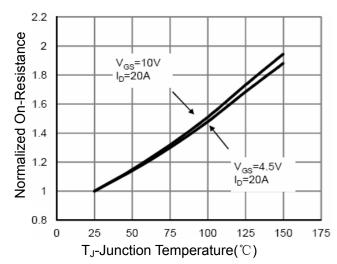
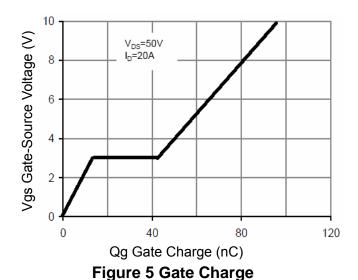


Figure 4 Rdson-JunctionTemperature



1.0E+02 € 1.0E+01 Is- Reverse Drain Current 125° C 1.0E+00 25° C 1.0E-01 1.0E-02 1.0E-03 1.0E-04 0.2 0.4 0.6 8.0 1.0 1.2 Vsd Source-Drain Voltage (V)

Figure 6 Source- Drain Diode Forward



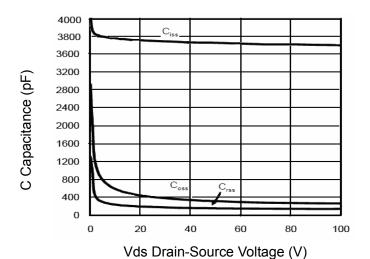


Figure 7 Capacitance vs Vds

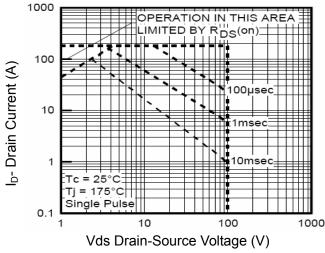


Figure 8 Safe Operation Area

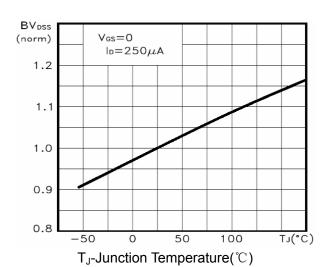


Figure 9 BV_{DSS} vs Junction Temperature

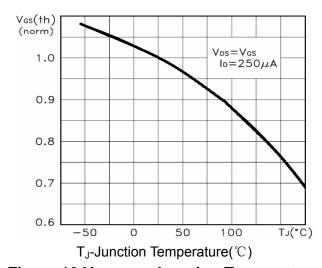


Figure 10 V_{GS(th)} vs Junction Temperature

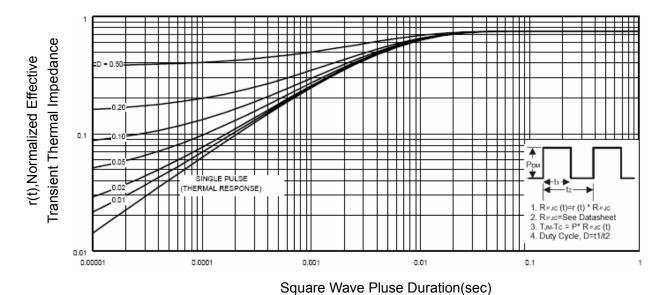
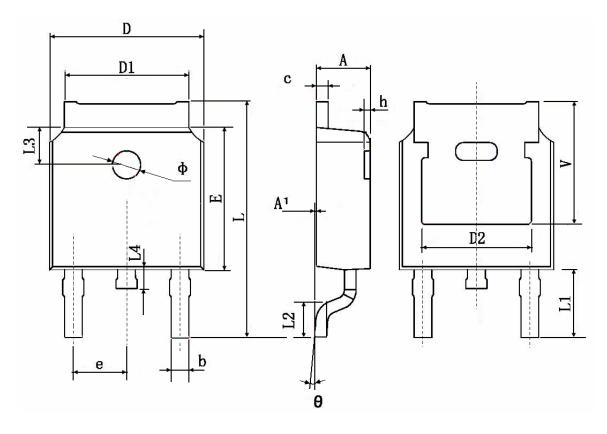


Figure 11 Normalized Maximum Transient Thermal Impedance



TO-252 Package Information



Symbol	Dimensions	In Millimeters	Dimensions In Inches		
	Min.	Max.	Min.	Max.	
A	2.200	2.400	0.087	0.094	
A1	0.000	0.127	0.000	0.005	
b	0.660	0.860	0.026	0.034	
С	0.460	0.580	0.018	0.023	
D	6.500	6.700	0.256	0.264	
D1	5.100	5.460	0.201	0.215	
D2	4.83	4.830 TYP. 0.190 TY			
Е	6.000	6.200	0.236	0.244	
е	2.186	2.386	0.086	0.094	
L	9.800	10.400	0.386	0.409	
L1	2.900	TYP.	0.114	TYP.	
L2	1.400	1.700	0.055	0.067	
L3	1.600	1.600 TYP.		TYP.	
L4	0.600	1.000	0.024	0.039	
Ф	1.100	1.300	0.043	0.051	
θ	0°	8°	0°	8°	
h	0.000	0.300	0.000	0.012	
V	5.350 TYP.		0.211 TYP.		



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